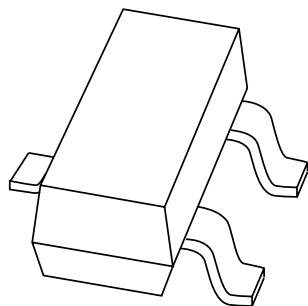


DATA SHEET



BSS64 NPN high voltage transistor

Product data sheet
Supersedes data of 2004 Jan 16

2004 Mar 12

NPN high voltage transistor

BSS64

FEATURES

- Low current (max. 100 mA)
- High voltage (max. 80 V).

APPLICATIONS

- High-voltage general purpose and switching applications
- Intended for thick and thin-film circuit applications.

DESCRIPTION

NPN transistor in a SOT23 plastic package.
PNP complement: BSS63.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
BSS64	60* or AM

Note

1. * = p: Made in Hong Kong.
- * = t: Made in Malaysia.
- * = W: Made in China.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BSS64	–	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	120	V
V_{CEO}	collector-emitter voltage	open base	–	80	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_C	collector current (DC)		–	100	mA
I_{CM}	peak collector current		–	250	mA
I_{BM}	peak base current		–	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25^\circ C$	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

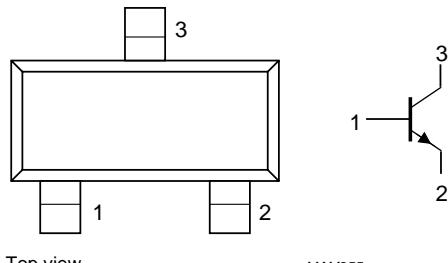


Fig.1 Simplified outline (SOT23) and symbol.

NPN high voltage transistor

BSS64

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$I_E = 0$; $V_{CB} = 90\text{ V}$	—	—	100	nA
		$I_E = 0$; $V_{CB} = 90\text{ V}$; $T_j = 150^\circ\text{C}$	—	—	50	μA
I_{EBO}	emitter-base cut-off current	$I_C = 0$; $V_{EB} = 5\text{ V}$	—	0.5	200	nA
h_{FE}	DC current gain	$I_C = 1\text{ mA}$; $V_{CE} = 1\text{ V}$	—	60	—	
		$I_C = 10\text{ mA}$; $V_{CE} = 1\text{ V}$	20	80	—	
		$I_C = 20\text{ mA}$; $V_{CE} = 1\text{ V}$	—	55	—	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 4\text{ mA}$; $I_B = 400\text{ }\mu\text{A}$	—	—	150	mV
		$I_C = 50\text{ mA}$; $I_B = 15\text{ mA}$	—	—	200	mV
C_c	collector capacitance	$I_E = I_e = 0$; $V_{CB} = 10\text{ V}$; $f = 1\text{ MHz}$	—	3	—	pF
f_T	transition frequency	$I_C = 4\text{ mA}$; $V_{CE} = 10\text{ V}$; $f = 100\text{ MHz}$	60	100	—	MHz

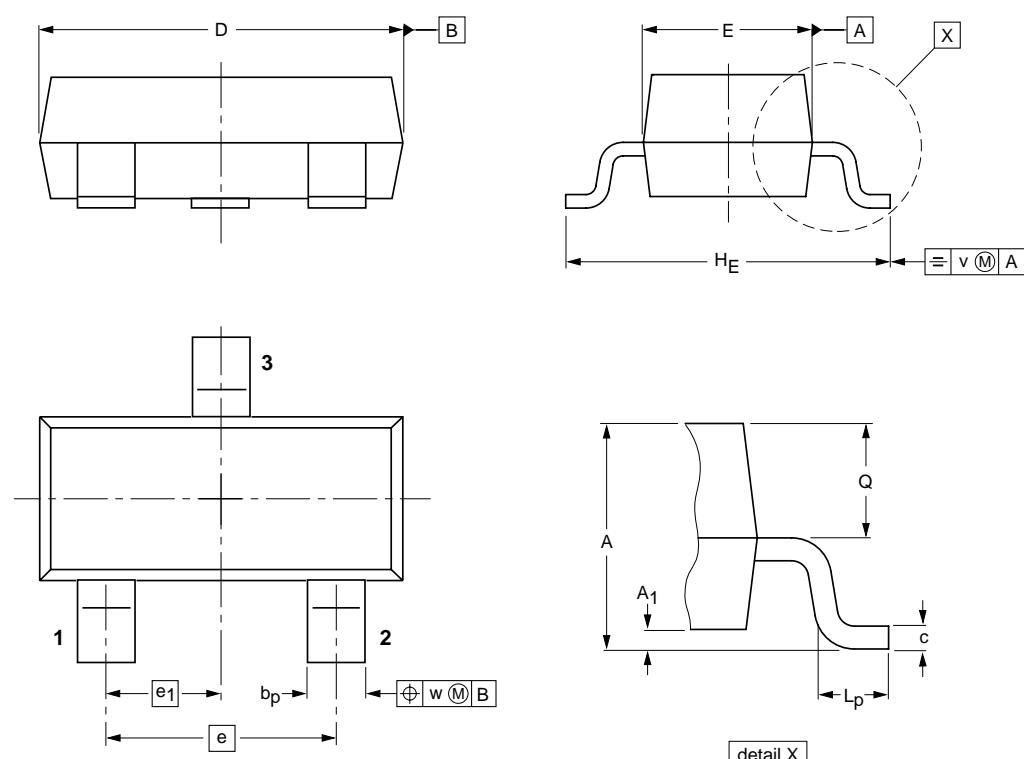
NPN high voltage transistor

BSS64

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

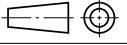
SOT23



0 1 2 mm
scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	l _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				-04-11-04- 06-03-16

NPN high voltage transistor

BSS64

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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